

3. (Amended) The three-dimensional device according to [one of claims 1 and 2, wherein] claim 1, further comprising a first substrate, the transfer method [comprises the steps of] comprising forming [a] the at least one thin film device layer on a [support] second substrate with a separable layer therebetween, and irradiating the separable layer with light to cause a separation in at least one of the separable layer [and/or] and at an interface so that the at least one thin film device layer on the [support] second substrate is transferred to [a] the first substrate of the three-dimensional device.

4. (Amended) The three-dimensional device according to claim 3, [wherein] the separation of the separable layer [is] being caused by one of breakage [or] and weakening of interatomic or intermolecular bonds in a material constituting the separable layer.

5. (Amended) The three-dimensional device according to claim 3, [wherein] the separation of the separable layer is caused by evolution of gas from a material constituting the separable layer.

6. (Amended) The three-dimensional device according to claim 3, [wherein] the light [is] being a laser beam.

7. (Amended) The three-dimensional device according to claim 3, [wherein] the separable layer [comprises any] comprising one of amorphous silicon, ceramic, metal, and organic polymeric material.

8. (Amended) The three-dimensional device according to [one of claims 1 and 2, wherein the] claim 1, each thin film device layer [comprises] comprising connecting electrodes[, the connecting electrodes] electrically connecting two adjacent thin film device layers to each other.

9. (Amended) The three-dimensional device according to claim 8, [wherein] the connecting electrodes [are] being provided on both surfaces of [the] each thin film device layer.

10. (Amended) The three-dimensional device according to claim 8, [wherein] further comprising an anisotropic conductive film, two adjacent thin film device layers [are] being joined to each other with [an] the anisotropic conductive film therebetween.

11. (Amended) The three-dimensional device according to [one of claims 1 and 2, wherein] claim 1, in two selected layers of the thin film device layers, [one] a first layer [has] having a light-emitting section and [the other] a second layer has a light-receiving section, the light-emitting section and the light-receiving section enabling optical communication between the two layers.

12. (Amended) The three-dimensional device according to [one of claims 1 and 2, wherein] claim 1, the at least one thin film device layer deposited by transferring [is] being formed simultaneously with at least one other of the [other] thin film device layers.

13. (Amended) The three-dimensional device according to [one of claims 1 and 2, wherein] claim 1, at least one of the thin film device layers [comprises] comprising a plurality of thin film transistors.

14. (Amended) The three-dimensional device according to [one of claims 1 and 2, wherein] claim 1, at least one of the thin film device layers [comprises] comprising a memory cell array.

15. The three-dimensional device according to [one of claims 1 and 2, wherein] claim 1, a plurality of layers among the thin film device layers [comprises] comprising one memory.

16. (Amended) The three-dimensional device according to [one of claims 1 and 2, wherein] claim 1, at least one of the thin film device layers [comprises] comprising a memory cell array, and at least one [of the] other thin film device layers comprises a logic circuit.

17. (Amended) The three-dimensional device according to claim 16, [wherein] the logic circuit [drives] driving the memory cell array.

18. (Amended) The three-dimensional device according to claim 16, [wherein] the logic circuit and the memory cell array [are] being formed in accordance with different design rules.

19. (Amended) The three-dimensional device according to claim 16, [wherein] the logic circuit and the memory cell array [are] being formed in accordance with different design parameters.

20. (Amended) The three-dimensional device according to claim 16, [wherein] the logic circuit and the memory cell array [are] being formed by different fabricating processes.

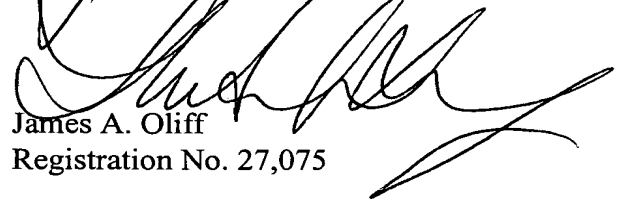
REMARKS

Claims 1-20 are pending. By this Amendment, the specification and claims 1-20 are amended. The specification and claims 1-20 are amended for further clarity. No new matter is added.

The above amendments place the application in even better condition for initial examination. Prompt consideration and allowance in due courses are earnestly solicited.

Should the Examiner believe that anything further is desirable in order to place this application in even better condition for allowance, the Examiner is requested to contact the Applicants' undersigned representative at the telephone number listed below.

Respectfully submitted,



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